

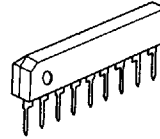
NJD6506/6507

The NJD6506 and NJD6507 each consist of four general purpose silicon NPN transistors on common emitter. The NJD6506 contains resistors for input bias.

■ Absolute Maximum Ratings (Ta=25°C)

Collector to Emitter Voltage	(6506) V _{CE}	20V
	(6507) V _{CEO}	20V
Collector to Base Voltage	(6507) V _{CBO}	25V
Emitter to Base Voltage	(6507) V _{EBO}	5V
Peak-to-Peak Collector	I _C MAX	200mA
Power Dissipation	P _D	500mW
Operating Temperature Range	T _{opr}	-20~+75°C
Storage Temperature Range	T _{stg}	-40~+125°C

■ Package Outline

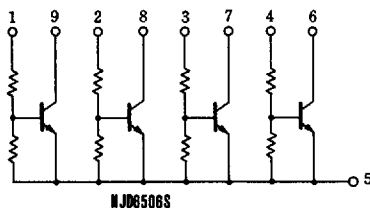


NJD6506S
NJD6507S

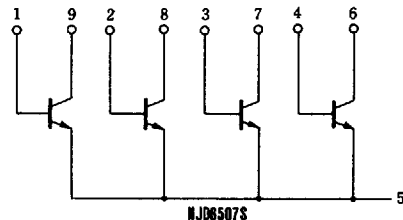
■ Electrical Characteristics (Ta=25°C)

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
6506						
Leakage Current	V ₀ =20V, V _{IN} =0.2V	I _L	—	—	2.0	μA
Output Voltage	V ⁺ =10V, V _{IN} =10V, R _L =400Ω	V _{CL}	—	—	120	mV
Output Voltage	V ⁺ =10V, V _{IN} =10V, R _L =10kΩ	V _{CL}	—	—	12.0	mV
Output Voltage	V ⁺ =10V, V _{IN} =0.2V, R _L =400Ω	V _{OH}	9.8	—	—	V
6507						
Collector to Emitter Cutoff Current	V _{CE} =20V	I _{CEO}	—	—	10	μA
Collector to Base Cutoff Current	V _{CB} =25V	I _{CBO}	—	—	1	μA
DC Current Gain	V _{CE} =6V, I _B =10μA	H _{FE}	60	—	600	
Base to Emitter Saturation Voltage	I _C =10mA, I _B =1mA	V _{BESAT}	—	—	0.95	V
Collector to Emitter Saturation Voltage	I _C =10mA, I _B =1mA	V _{CESAT}	—	—	0.2	V
Collector to Emitter Saturation Voltage	I _C =50mA, I _B =5mA	V _{CESAT}	—	—	0.5	V

■ Equivalent Circuit & Pin Connection



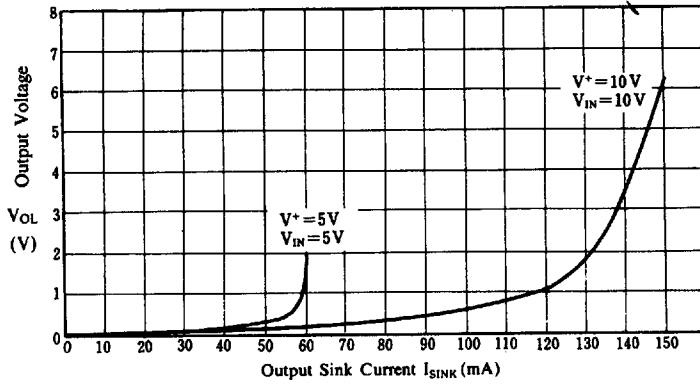
All resistor is 20kΩ type.



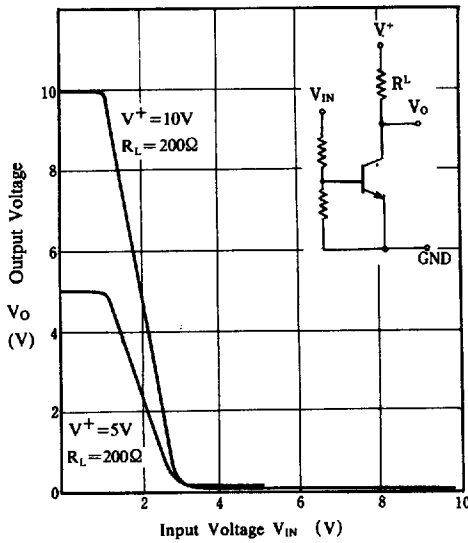
Note: Five transistors in 14-Lead Dual In Line package is available.

■ Typical Characteristics

NJD6506 Output Voltage vs. Output Sink Current
($T_a = 25^\circ\text{C}$)



NJD6506 Input Voltage vs. Output Voltage
($T_a = 25^\circ\text{C}$)



NJD6507 Collector Current vs. Collector to Emitter Voltage
($T_a = 25^\circ\text{C}$)

